

Title (en)
WAFER PRODUCTION METHOD

Title (de)
VERFAHREN ZUR WAFERHERSTELLUNG

Title (fr)
PROCÉDÉ DE PRODUCTION DE PLAQUETTE

Publication
EP 2033739 B1 20110921 (EN)

Application
EP 07743143 A 20070511

Priority

- JP 2007059708 W 20070511
- JP 2006159988 A 20060608

Abstract (en)
[origin: EP2033739A1] The present invention is a wafer production method at least comprising a chamfering step of chamfering a wafer sliced from an ingot using a grindstone for chamfering, and a step of obtaining a product wafer thinner than the chamfered wafer by performing at least one or more than one of the following processes on the chamfered wafer: flattening, etching, and polishing, the method at least comprising a correction step of chamfering a dummy wafer equivalent in thickness to the product wafer, measuring the chamfered dummy wafer for its chamfered shape, and correcting the shape of the grindstone for chamfering based on the measured chamfered shape of the dummy wafer, at least before the chamfering step, thereby chamfering the wafer sliced from the ingot using the grindstone for chamfering having its shape corrected. Thus, it is possible to provide a wafer production method allowing a product wafer with a desired chamfered shape to be obtained in a short period of time.

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